

# D1N60

# SILICON RECTIFIER DIODE

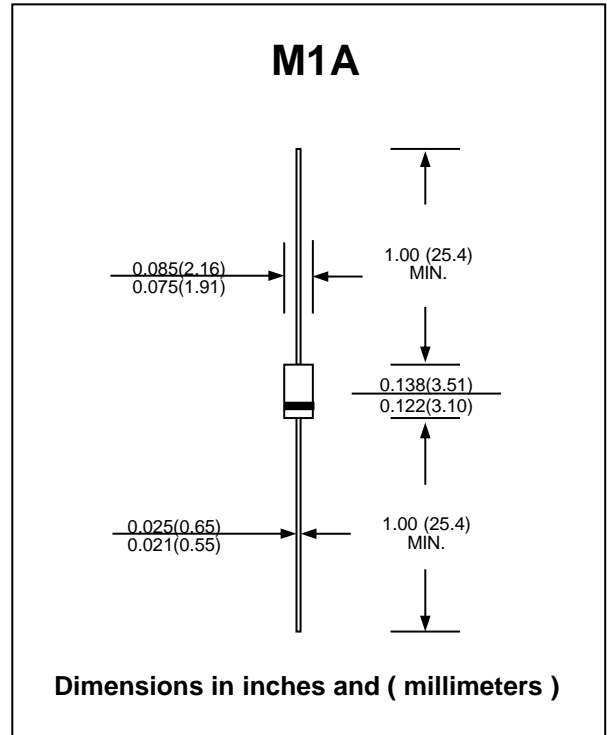
**PRV : 600 Volts**  
**Io : 1.0 Amperes**

## FEATURES :

- \* Glass passivated junction chip
- \* High current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* **Pb / RoHS Free**

## MECHANICAL DATA :

- \* Case : M1A Molded plastic
- \* Epoxy : UL94V-0 rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.20 gram (approximately)



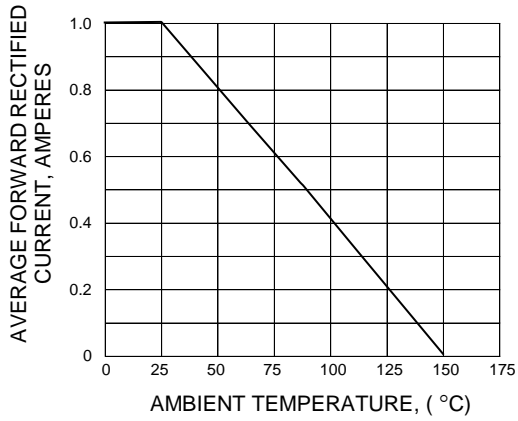
## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C Lead temperature unless otherwise specified.

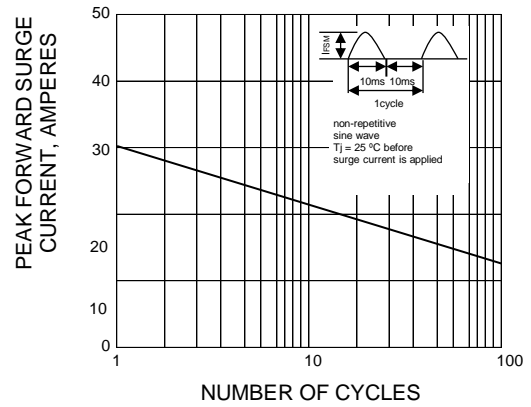
RATING	SYMBOL	VALUE	UNIT
Maximum Peak Reverse Voltage	$V_{RRM}$	600	V
Maximum RMS Voltage	$V_{RMS}$	420	V
Maximum DC Blocking Voltage	$V_{DC}$	600	V
Maximum Average Forward Current ( 50 Hz sine wave, R-load, $T_a = 25^\circ\text{C}$ )	$I_{F(AV)}$	1.0	A
Maximum Peak Forward Surge Current ( 50 Hz sine wave, Non - repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$ )	$I_{FSM}$	30	A
Maximum Peak Forward Voltage at $I_F = 1.0\text{ A}$ , Pulse measurement	$V_F$	1.05	V
Maximum DC Reverse Current at $V_{RRM}$ , Pulse measurement	$I_R$	10	$\mu\text{A}$
Maximum Thermal Resistance (Junction to lead)	$R_{\theta JL}$	10	$^\circ\text{C/W}$
Maximum Thermal Resistance (Junction to ambient)	$R_{\theta JA}$	113	$^\circ\text{C/W}$
Junction Temperature Range	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 55 to + 150	$^\circ\text{C}$

## RATING AND CHARACTERISTIC CURVES (D1N60)

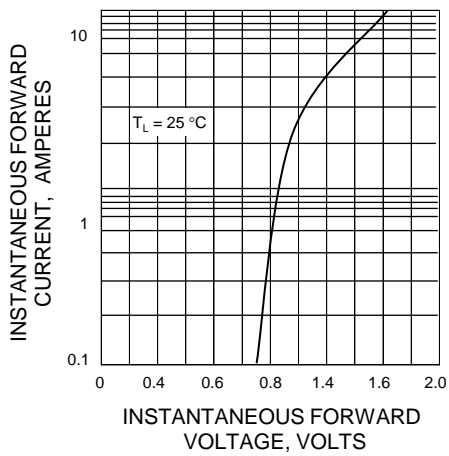
**FIG.1 - FORWARD CURRENT DERATING CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS**



**FIG. 4 - FORWARD POWER DISSIPATION**

